

LD H9GP

OSLON® Black

OSLON Black Series combines thermal stability with high performance and reliability in a compact black package. It has a metal lead frame and a tried and tested lens design. The LED can be used wherever there are large fluctuations in temperature and a large amount of light is needed from a small area.



Applications

- Cluster, Button Backlighting
- Custom Tuning
- Head-Up Display LED & Laser
- Interior Illumination (e.g. Ambient Map)
- Transportation, Plane, Ship

Features:

- Package: SMD epoxy package with silicone lens
- Chip technology: ThinGaN
- Typ. Radiation: 90°
- Color: $\lambda_{\text{dom}} = 455 \text{ nm}$ (● deep blue)
- Corrosion Robustness Class: 3B
- Qualifications: The product qualification test plan is based on the guidelines of AEC-Q101-REV-C, Stress Test Qualification for Automotive Grade Discrete Semiconductors.
- ESD: 8 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 3B)

Ordering Information

Type	Total radiant flux ¹⁾ $I_F = 350 \text{ mA}$ Φ_E	Ordering Code
LD H9GP-3T2U-35-1	355 ... 560 mW	Q65111A1709

Maximum Ratings

Parameter	Symbol		Values
Operating Temperature	T_{op}	min.	-40 °C
		max.	125 °C
Storage Temperature	T_{stg}	min.	-40 °C
		max.	125 °C
Junction Temperature	T_j	max.	150 °C
Junction Temperature for short time applications*	T_j	max.	175 °C
Forward current	I_F	min.	100 mA
$T_s = 25\text{ °C}$		max.	1000 mA
Surge Current	I_{FS}	max.	2500 mA
$t \leq 10\text{ }\mu\text{s}$; $D = 0.016$; $T_s = 25\text{ °C}$			
ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 3B)	V_{ESD}		8 kV
Reverse current ²⁾	I_R	max.	200 mA

*The median lifetime (L70/B50) for $T_j = 175\text{ °C}$ is 100h.

Characteristics

$I_F = 350 \text{ mA}$; $T_s = 25 \text{ °C}$

Parameter	Symbol		Values
Peak Wavelength ³⁾	λ_{peak}	typ.	449 nm
Dominant Wavelength ³⁾	λ_{dom}	min.	449 nm
$I_F = 350 \text{ mA}$		typ.	455 nm
		max.	461 nm
Spectral Bandwidth at 50% $I_{\text{rel,max}}$	$\Delta\lambda$	typ.	20 nm
Viewing angle at 50 % I_V	2ϕ	typ.	90 °
Forward Voltage ⁴⁾	V_F	min.	2.75 V
$I_F = 350 \text{ mA}$		typ.	3.20 V
		max.	3.75 V
Reverse voltage (ESD device)	V_{RESD}	min.	45 V
Reverse voltage ²⁾	V_R	max.	1.2 V
$I_R = 20 \text{ mA}$			
Real thermal resistance junction/solderpoint ⁵⁾	$R_{\text{thJS real}}$	typ.	6.5 K / W
		max.	11.0 K / W

Brightness Groups

Group	Total radiant flux ¹⁾ $I_F = 350 \text{ mA}$ min. Φ_E	Total radiant flux ¹⁾ $I_F = 350 \text{ mA}$ max. Φ_E
3T	355 mW	400 mW
4T	400 mW	450 mW
1U	450 mW	500 mW
2U	500 mW	560 mW

Forward Voltage Groups

Group	Forward Voltage ⁴⁾ $I_F = 350 \text{ mA}$ min. V_F	Forward Voltage ⁴⁾ $I_F = 350 \text{ mA}$ max. V_F
8E	2.75 V	3.00 V
8F	3.00 V	3.25 V
8G	3.25 V	3.50 V
8H	3.50 V	3.75 V

Wavelength Groups

Group	Dominant Wavelength ³⁾ $I_F = 350 \text{ mA}$ min. λ_{dom}	Dominant Wavelength ³⁾ $I_F = 350 \text{ mA}$ max. λ_{dom}
3	449 nm	453 nm
4	453 nm	457 nm
5	457 nm	461 nm

Group Name on Label

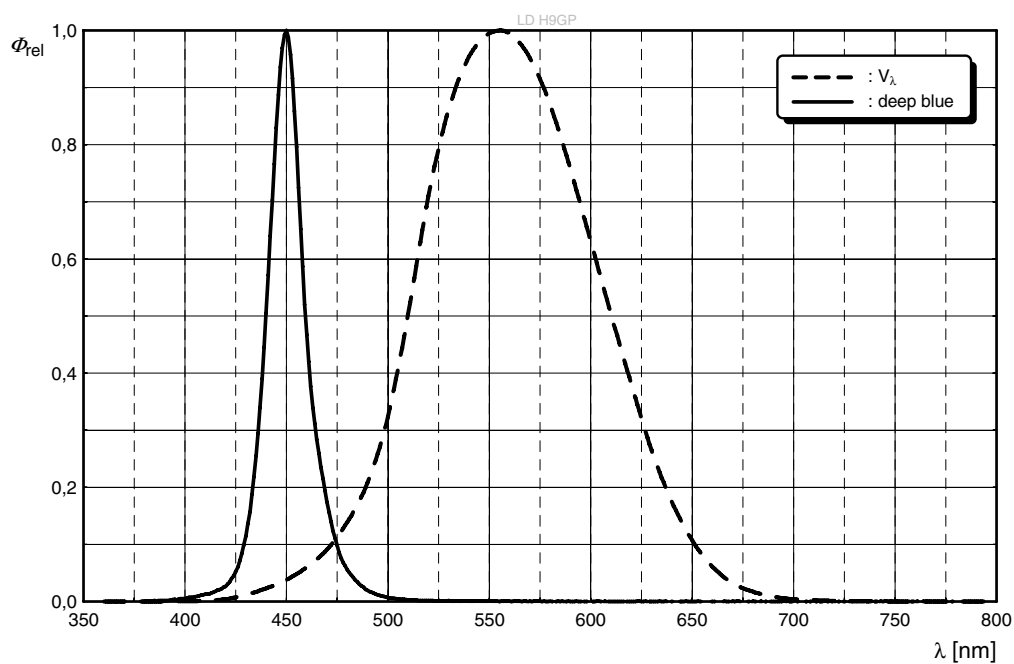
Example: 1U-3-8E

Brightness	Wavelength	Forward Voltage
1U	3	8E

Discontinued

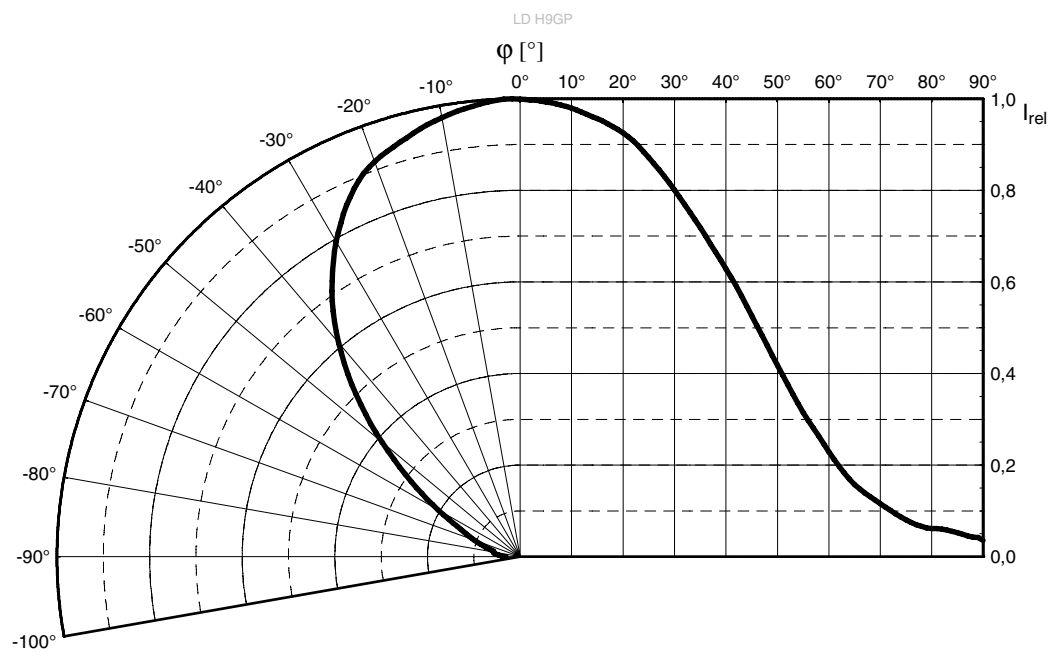
Relative Spectral Emission ⁶⁾

$$\Phi_{\text{rel}} = f(\lambda); I_F = 350 \text{ mA}; T_S = 25^\circ\text{C}$$



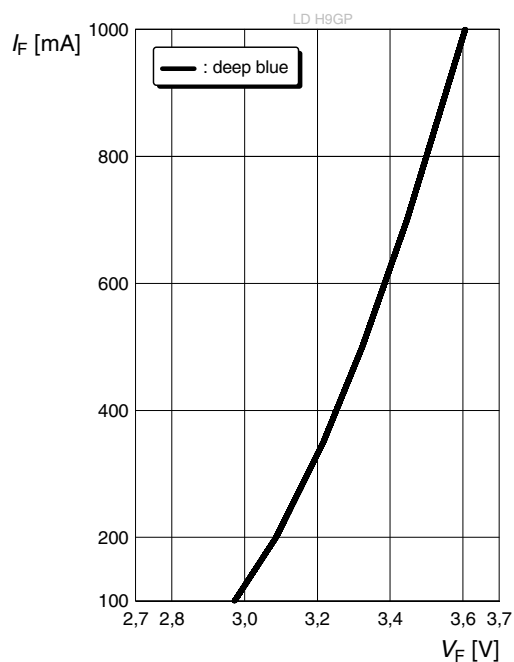
Radiation Characteristics ⁶⁾

$$I_{\text{rel}} = f(\phi); T_S = 25^\circ\text{C}$$

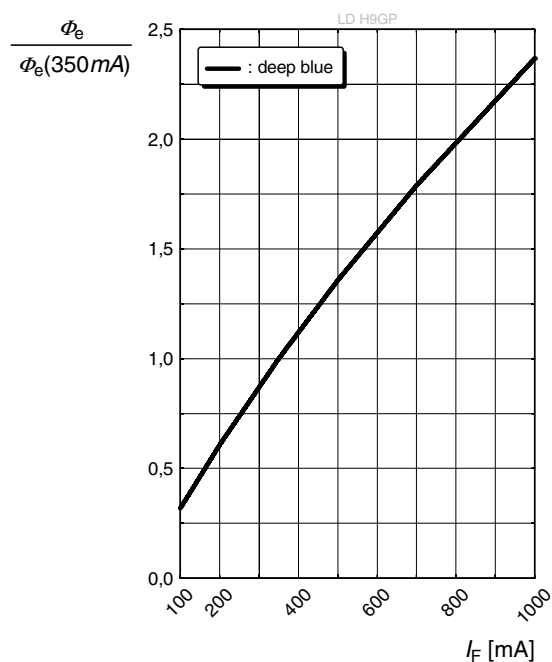


Forward current ^{6), 7)}

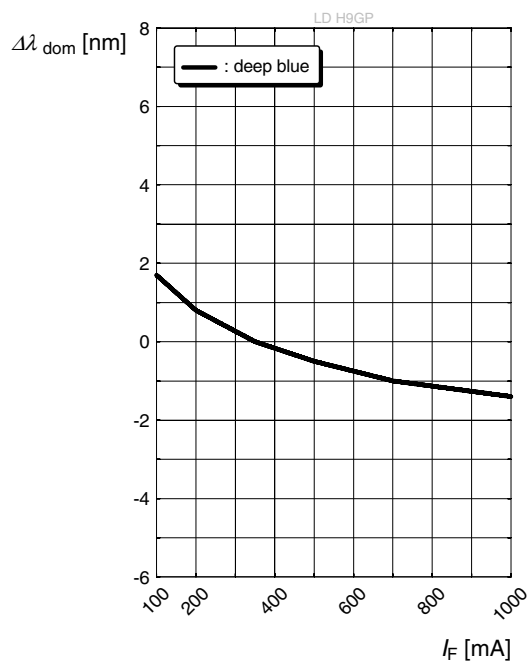
$$I_F = f(V_F); T_S = 25\text{ °C}$$

**Relative Radiant Power** ^{6), 7)}

$$\Phi_E / \Phi_E(350\text{ mA}) = f(I_F); T_S = 25\text{ °C}$$

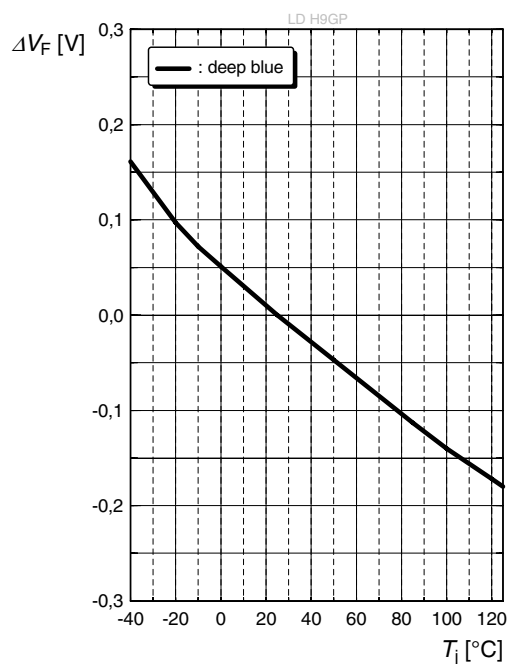
**Dominant Wavelength** ⁶⁾

$$\Delta\lambda_{\text{dom}} = f(I_F); T_S = 25\text{ °C}$$

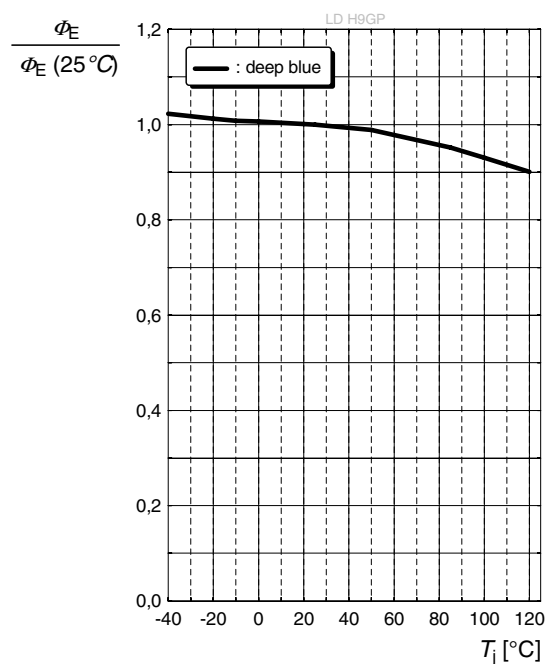


Forward Voltage ⁶⁾

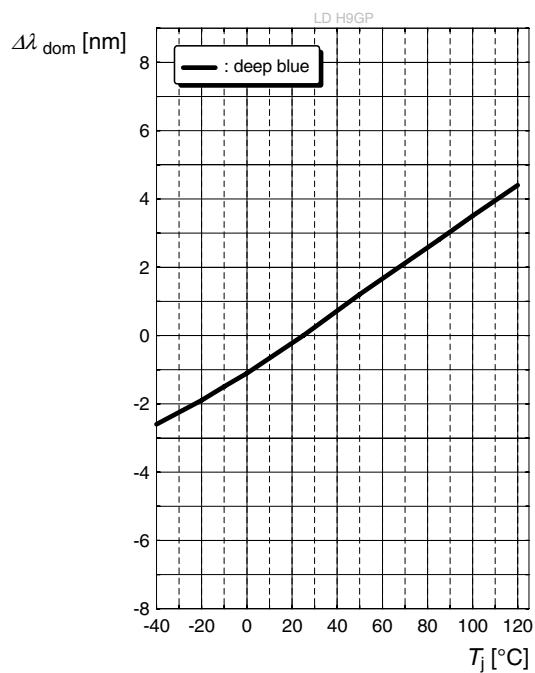
$$\Delta V_F = V_F - V_F(25^\circ\text{C}) = f(T_j); I_F = 350\text{ mA}$$

**Relative Radiant Power** ⁶⁾

$$\Phi_E / \Phi_E(25^\circ\text{C}) = f(T_j); I_F = 350\text{ mA}$$

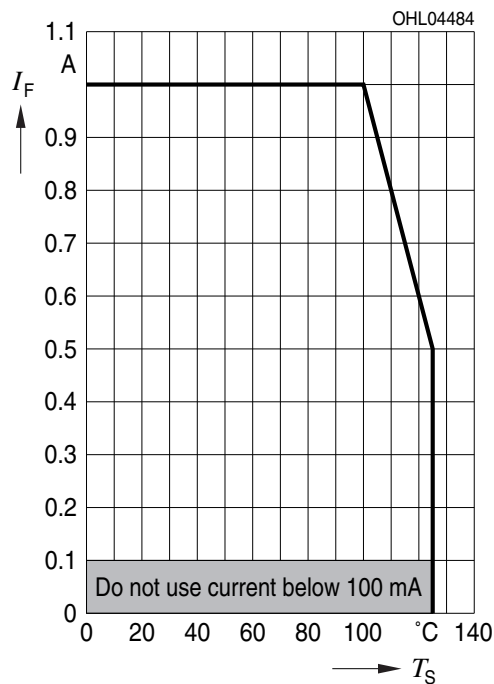
**Dominant Wavelength** ⁶⁾

$$\Delta \lambda_{\text{dom}} = \lambda_{\text{dom}} - \lambda_{\text{dom}}(25^\circ\text{C}) = f(T_j); I_F = 350\text{ mA}$$



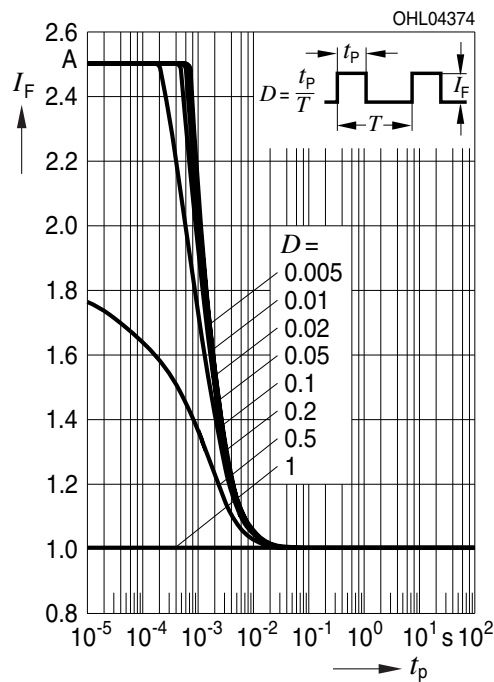
Max. Permissible Forward Current

$$I_F = f(T)$$



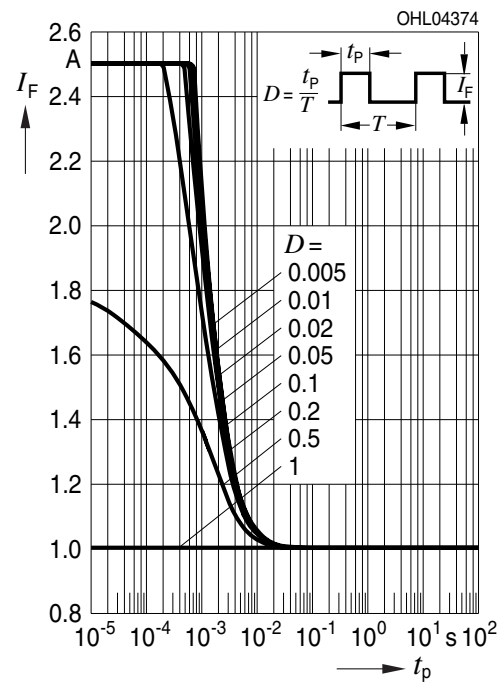
Permissible Pulse Handling Capability

$$I_F = f(t_p); D: \text{Duty cycle}; T_S = 25^\circ\text{C}$$

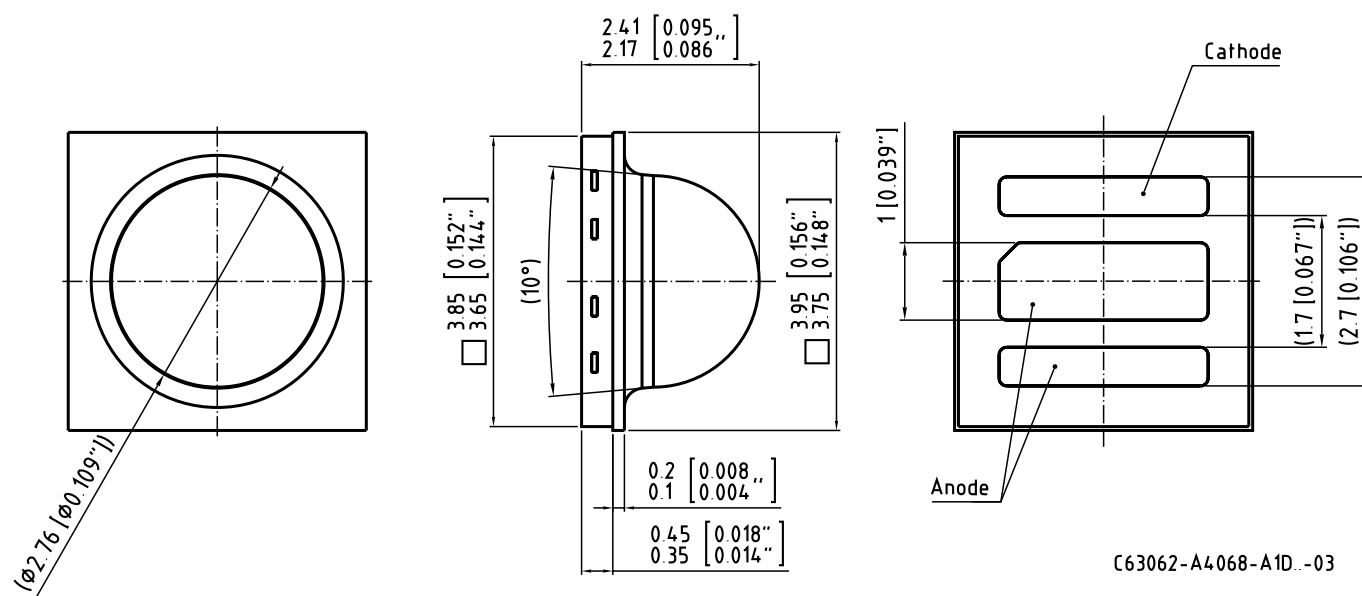


Permissible Pulse Handling Capability

$$I_F = f(t_p); D: \text{Duty cycle}; T_S = 85^\circ\text{C}$$



Dimensional Drawing ⁸⁾



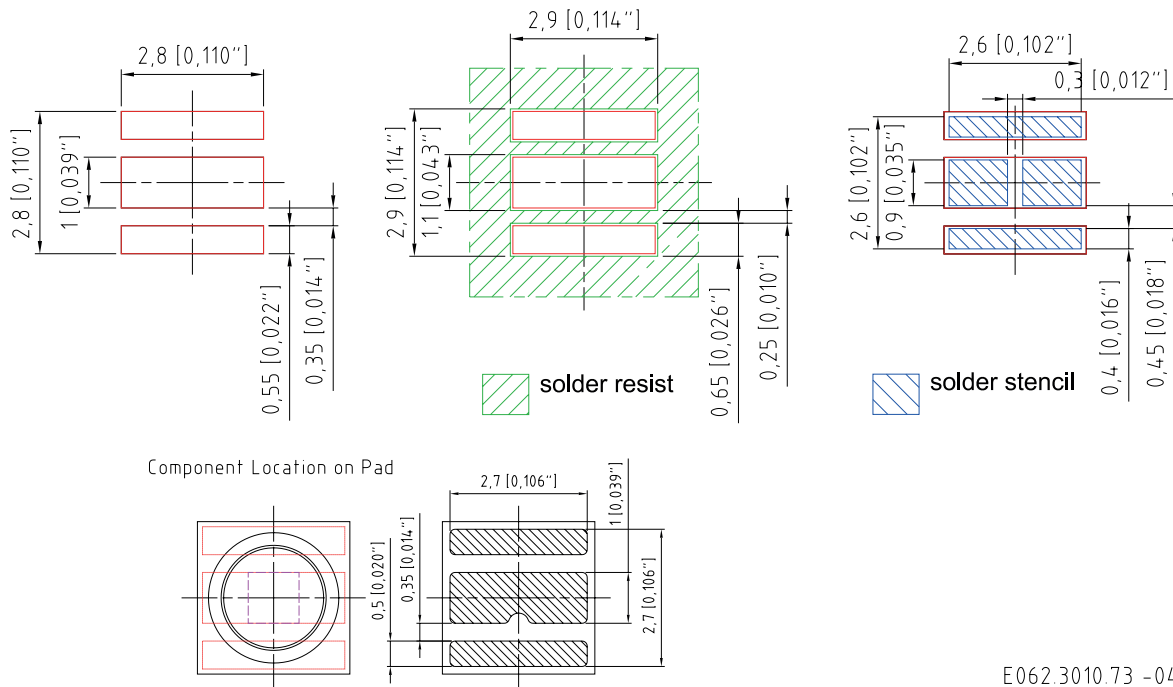
Approximate Weight: 32.0 mg

Package marking: Cathode

Corrosion test: Class: 3B
 Test condition: 40°C / 90 % RH / 15 ppm H₂S / 14 days (stricter than IEC 60068-2-43)

ESD advice: The device is protected by ESD device which is connected in parallel to the Chip.

Recommended Solder Pad ⁸⁾



E062.3010.73 -04

For superior solder joint connectivity results we recommend soldering under standard nitrogen atmosphere. In case the PCB layout of the application is intended to be used with other OSRON derivatives or in future developed OSRON derivatives, the heat sink must not be electrically connected to anode or cathode solder pad because of possible chip inverted polarity. Package not suitable for ultra sonic cleaning.

Reflow Soldering Profile

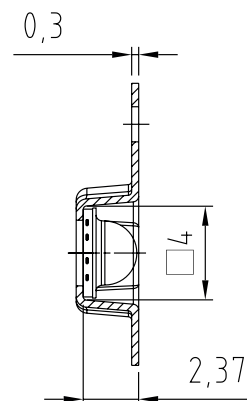
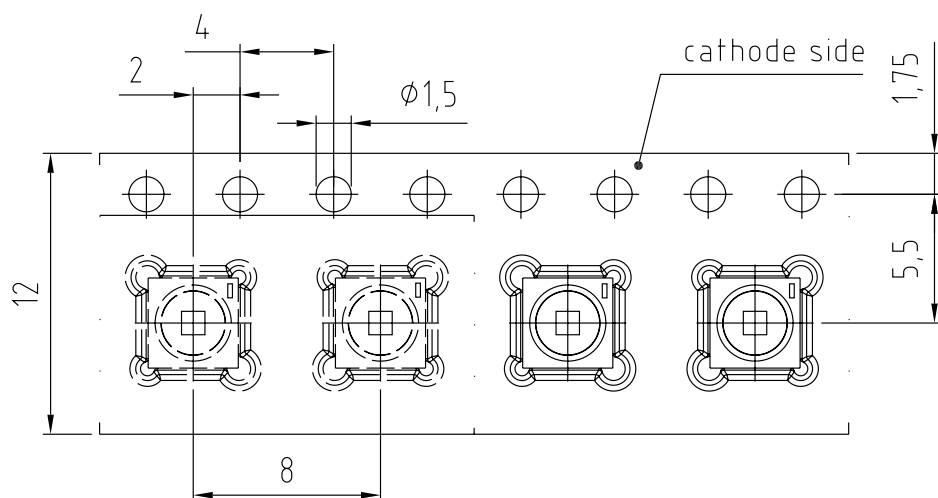
Product complies to MSL Level 2 acc. to JEDEC J-STD-020E



Profile Feature	Symbol	Pb-Free (SnAgCu) Assembly			Unit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat ^{*)} 25 °C to 150 °C			2	3	K/s
Time t_s T_{Smin} to T_{Smax}	t_s	60	100	120	s
Ramp-up rate to peak ^{*)} T_{Smax} to T_p			2	3	K/s
Liquidus temperature	T_L		217		$^{\circ}\text{C}$
Time above liquidus temperature	t_L		80	100	s
Peak temperature	T_p		245	260	$^{\circ}\text{C}$
Time within 5 °C of the specified peak temperature $T_p - 5\text{ K}$	t_p	10	20	30	s
Ramp-down rate* T_p to 100 °C			3	6	K/s
Time 25 °C to T_p				480	s

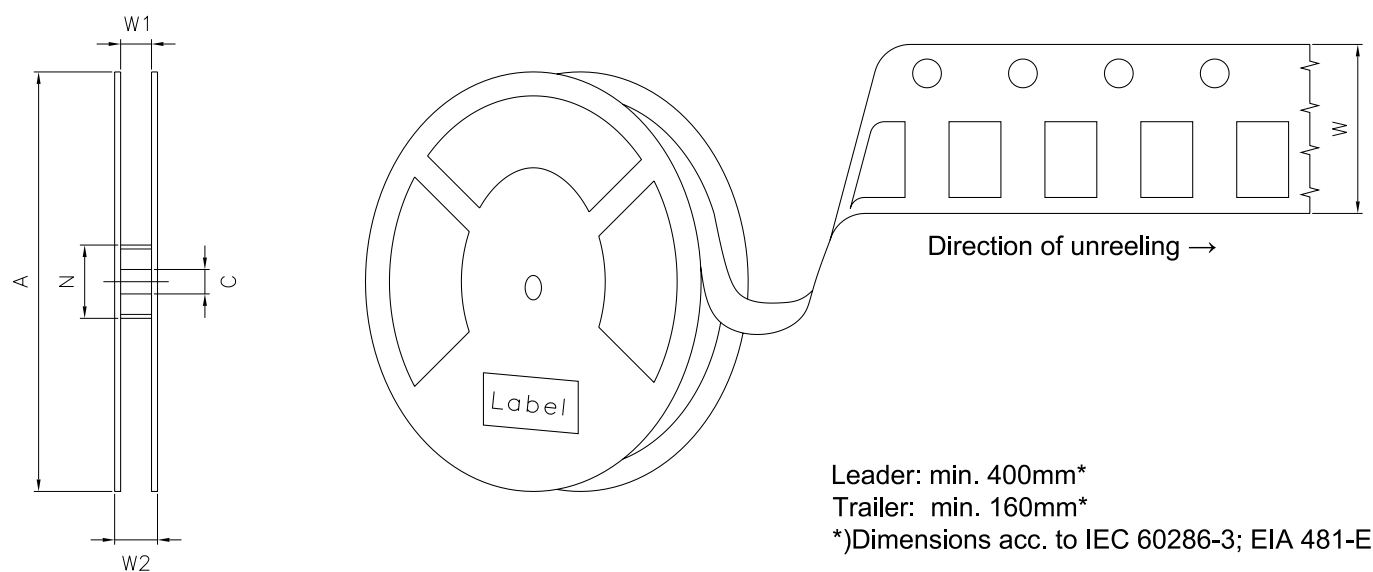
All temperatures refer to the center of the package, measured on the top of the component

* slope calculation DT/Dt : Dt max. 5 s; fulfillment for the whole T-range

Taping ⁸⁾

C63062-A4068-B10 -12

Tape and Reel ⁹⁾



Reel dimensions [mm]

A	W	N _{min}	W ₁	W _{2 max}	Pieces per PU
180 mm	12 + 0.3 / - 0.1	60	12.4 + 2	18.4	600
330 mm	12 + 0.3 / - 0.1	60	12.4 + 2	18.4	3000

Barcode-Product-Label (BPL)

OSRAM Opto Semiconductors

LX XXXX BIN1: XX-XX-X-XXX-X

RoHS Compliant

(6P) BATCH NO: 1234567890

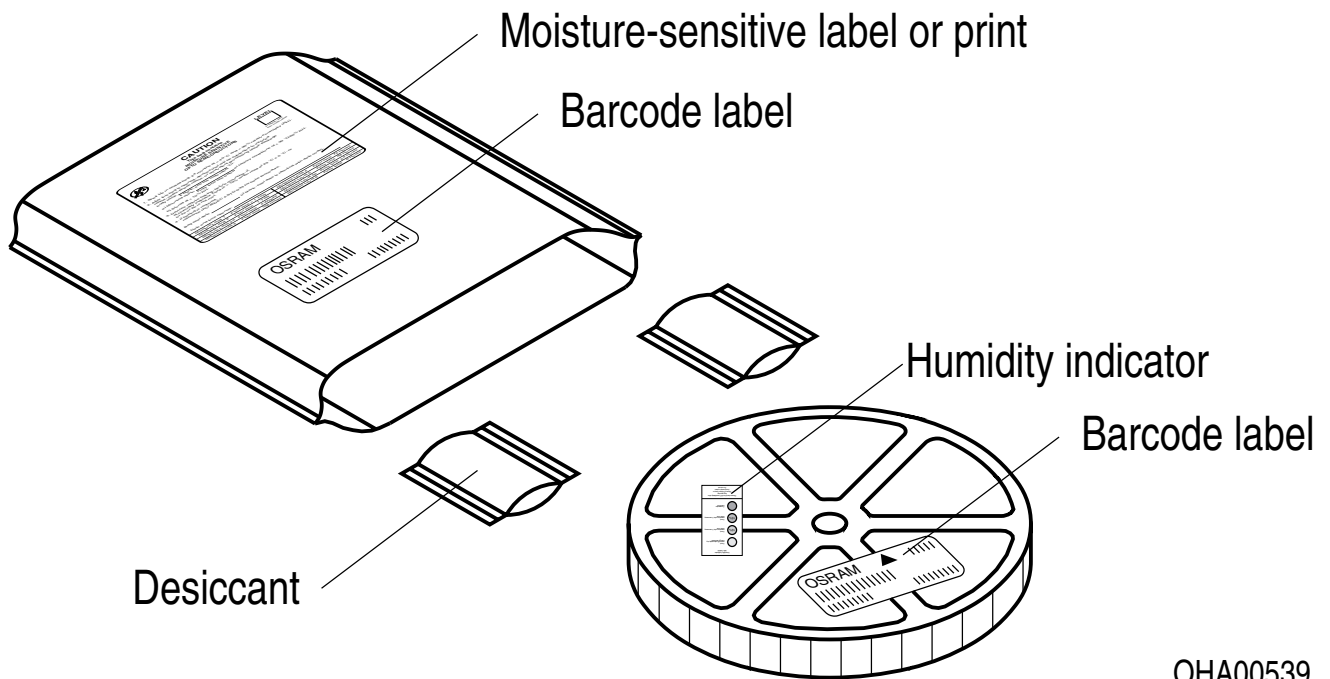
(1T) LOT NO: 1234567890 (9D) D/C: 1234

ML Temp ST
X XXX °C X

Pack: RXX
DEMY XXX
X_X123_1234.1234 X

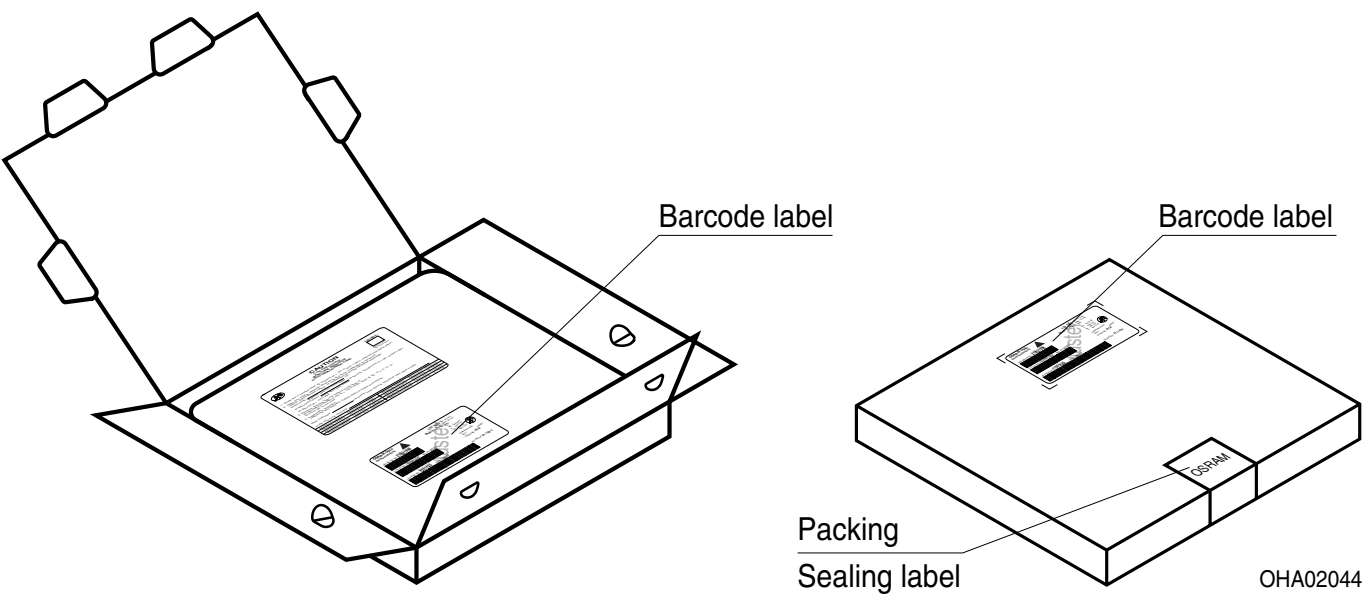
(X) PROD NO: 123456789 (Q) QTY: 9999 (G) GROUP: XX-XX-X-X

OHA04563

Dry Packing Process and Materials ⁸⁾

Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card according JEDEC-STD-033.

Transportation Packing and Materials ⁸⁾

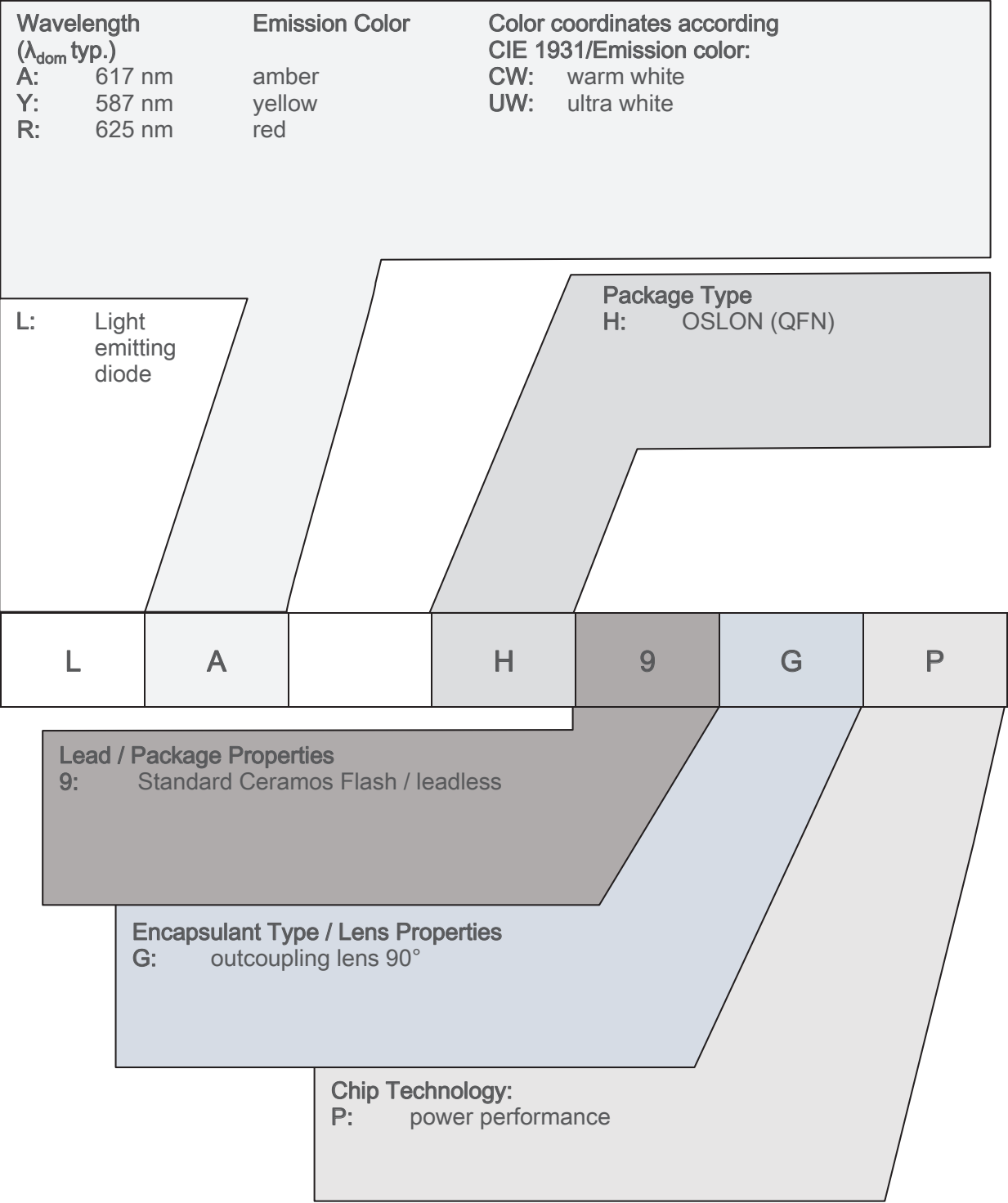


Dimensions of transportation box in mm

Width	Length	Height
195 ± 5 mm	195 ± 5 mm	30 ± 5 mm
349 ± 5 mm	349 ± 5 mm	33 ± 5 mm



Type Designation System



Discontinued

Notes

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet falls into the class **moderate risk (exposure time 0.25 s)**. Under real circumstances (for exposure time, conditions of the eye pupils, observation distance), it is assumed that no endangerment to the eye exists from these devices. As a matter of principle, however, it should be mentioned that intense light sources have a high secondary exposure potential due to their blinding effect. When looking at bright light sources (e.g. headlights), temporary reduction in visual acuity and afterimages can occur, leading to irritation, annoyance, visual impairment, and even accidents, depending on the situation.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related informations please visit www.osram-os.com/appnotes

Disclaimer

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on the OSRAM OS website.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office.

By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Product safety devices/applications or medical devices/applications

OSRAM OS components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

In case Buyer – or Customer supplied by Buyer– considers using OSRAM OS components in product safety devices/applications or medical devices/applications, Buyer and/or Customer has to inform the local sales partner of OSRAM OS immediately and OSRAM OS and Buyer and /or Customer will analyze and coordinate the customer-specific request between OSRAM OS and Buyer and/or Customer.

Glossary

- 1) **Brightness:** Brightness values are measured during a current pulse of typically 25 ms, with an internal reproducibility of $\pm 8\%$ and an expanded uncertainty of $\pm 11\%$ (acc. to GUM with a coverage factor of $k = 3$).
- 2) **Reverse Operation:** Reverse Operation of 10 hours is permissible in total. Continuous reverse operation is not allowed.
- 3) **Wavelength:** The wavelength is measured at a current pulse of typically 25 ms, with an internal reproducibility of $\pm 0.5\text{ nm}$ and an expanded uncertainty of $\pm 1\text{ nm}$ (acc. to GUM with a coverage factor of $k = 3$).
- 4) **Forward Voltage:** The forward voltage is measured during a current pulse of typically 8 ms, with an internal reproducibility of $\pm 0.05\text{ V}$ and an expanded uncertainty of $\pm 0.1\text{ V}$ (acc. to GUM with a coverage factor of $k = 3$).
- 5) **Thermal Resistance:** $R_{th\text{ max}}$ is based on statistic values (6σ).
- 6) **Typical Values:** Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- 7) **Characteristic curve:** In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- 8) **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ± 0.1 and dimensions are specified in mm.
- 9) **Tape and Reel:** All dimensions and tolerances are specified acc. IEC 60286-3 and specified in mm.

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EU RoHS and China RoHS compliant product



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按照中国的相关法规和标准，不含有毒有害物质或元素。